

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device having a
5 semiconductor multi-layer structure which includes at least an active layer
having at least a quantum well, and the active layer further including at
least a luminescent layer of $In_xAl_yGa_{1-x-y}N$ ($0 < x < 1$, $0 \leq y \leq 0.2$), wherein a
threshold mode gain of each of the at least quantum well is not more than
12 cm^{-1} , and wherein a standard deviation of a microscopic fluctuation in a
10 band gap energy of the at least luminescent layer is in the range of 75 meV
to 200 meV.